

THE LETI NIL ASSESSMENT PLATFORM

LETI Lithography Workshop SPIE 2018 NIL session



WHICH PROBLEMS COULD BE ADDRESSED WITH THIS TECHNOLOGY







THE MAIN INSPIRE PROGRAM OBJECTIVES









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DISTORSION IMPROVEMENT





THE 2018 ROADMAP

	Q1	Q2	Q3	Q4
Materials	Filters in tool qualification	< 200 particles [90-500nm] in MOR film	Imprint materials benchmark	imprint resist prod. ready for etch mask app.
Overlay	< 1 µm wafer scale	< 1 µm / 4" area w2w & lot 2 lot repeatability	< 1 µm / 6" area w2w & lot 2 lot repeatability	< 1 µm / 8" area w2w & lot 2 lot repeatability
Production	Imprint fingerprint stability assessment	Metrology and Master platform access	Reference 100 nm produc Yield > 50%	Reference 100 nm produc Yield > 80%
Integration	100 nm feat. AR 1 in dielectric mat. transfer	50 nm feat. AR 1 in dielectric mat. transfer	20 nm feat. AR 1 in dielectric mat. transfer	Mix and match with DUV tools

THE NEXT STEPS FOR FURTHER ASSESSMENT AND VALIDATION

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